

BC547 BC547A BC547B BC547C



NPN General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 10. See PN100A for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	45	V
V _{CES}	Collector-Base Voltage	50	V
V _{EBO}	Emitter-Base Voltage	6.0	V
I _C	Collector Current - Continuous	500	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

These ratings are based on a maximum junction temperature of 150 degrees C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		BC547 / A / B / C	
P_D	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

NPN General Purpose Amplifier (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
	DACTEDICTICS				
	RACTERISTICS	1 40 1 0	45	Т	V
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0$	45		·
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10 \mu A, I_E = 0$	50		V
V _{(BR)CES}	Collector-Base Breakdown Voltage	$I_C = 10 \mu A, I_E = 0$	50		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	6.0		V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 30 \text{ V}, I_{E} = 0$		15	nA
020		$V_{CB} = 30 \text{ V}, I_{E} = 0, T_{A} = +150 \text{ °C}$		5.0	μΑ
	ACTERISTICS DC Current Gain	V _{CE} = 5.0 V. I _C = 2.0 mA 547	110	800	
ON CHAR		547A	110	220	
		547A 547B	110 200	220 450	
h _{FE}	DC Current Gain	547A 547B 547C	110	220 450 800	
h _{FE}		547A 547B 547C I _C = 10 mA, I _B = 0.5 mA	110 200	220 450 800 0.25	V
h_{FE}	DC Current Gain	547A 547B 547C	110 200	220 450 800	V
h_{FE}	DC Current Gain Collector-Emitter Saturation Voltage	547A 547B 547C I _C = 10 mA, I _B = 0.5 mA I _C = 100 mA, I _B = 5.0 mA	110 200 420	220 450 800 0.25 0.60	V
h _{FE}	DC Current Gain Collector-Emitter Saturation Voltage	$\begin{array}{c} \textbf{547A} \\ \textbf{547B} \\ \textbf{547C} \\ \\ \textbf{I}_{C} = 10 \text{ mA, I}_{B} = 0.5 \text{ mA} \\ \textbf{I}_{C} = 100 \text{ mA, I}_{B} = 5.0 \text{ mA} \\ \\ \textbf{V}_{CE} = 5.0 \text{ V, I}_{C} = 2.0 \text{ mA} \\ \end{array}$	110 200 420	220 450 800 0.25 0.60 0.70	V
V _{CE(sat)}	DC Current Gain Collector-Emitter Saturation Voltage	$\begin{array}{c} \textbf{547A} \\ \textbf{547B} \\ \textbf{547C} \\ \\ \textbf{I}_{C} = 10 \text{ mA, I}_{B} = 0.5 \text{ mA} \\ \textbf{I}_{C} = 100 \text{ mA, I}_{B} = 5.0 \text{ mA} \\ \\ \textbf{V}_{CE} = 5.0 \text{ V, I}_{C} = 2.0 \text{ mA} \\ \end{array}$	110 200 420	220 450 800 0.25 0.60 0.70	V
h_{FE} $V_{CE(sat)}$ $V_{BE(on)}$	DC Current Gain Collector-Emitter Saturation Voltage Base-Emitter On Voltage	$\begin{array}{c} \textbf{547A} \\ \textbf{547B} \\ \textbf{547C} \\ \\ \textbf{I}_{C} = 10 \text{ mA, I}_{B} = 0.5 \text{ mA} \\ \textbf{I}_{C} = 100 \text{ mA, I}_{B} = 5.0 \text{ mA} \\ \\ \textbf{V}_{CE} = 5.0 \text{ V, I}_{C} = 2.0 \text{ mA} \\ \\ \textbf{V}_{CE} = 5.0 \text{ V, I}_{C} = 10 \text{ mA} \\ \\ \\ \textbf{I}_{C} = 2.0 \text{ mA, V}_{CE} = 5.0 \text{ V,} \\ \\ \end{array}$	110 200 420	220 450 800 0.25 0.60 0.70	V
$\begin{array}{c} h_{\text{FE}} \\ \\ V_{\text{CE(sat)}} \\ \\ V_{\text{BE(on)}} \\ \\ \\ SMALL \ S \\ \\ h_{\text{fe}} \\ \\ \end{array}$	DC Current Gain Collector-Emitter Saturation Voltage Base-Emitter On Voltage IGNAL CHARACTERISTICS Small-Signal Current Gain	$\begin{array}{c} \textbf{547A} \\ \textbf{547B} \\ \textbf{547C} \\ \\ \textbf{I}_{C} = 10 \text{ mA, I}_{B} = 0.5 \text{ mA} \\ \textbf{I}_{C} = 100 \text{ mA, I}_{B} = 5.0 \text{ mA} \\ \\ \textbf{V}_{CE} = 5.0 \text{ V, I}_{C} = 2.0 \text{ mA} \\ \\ \textbf{V}_{CE} = 5.0 \text{ V, I}_{C} = 10 \text{ mA} \\ \end{array}$	110 200 420 0.58	220 450 800 0.25 0.60 0.70 0.77	V V V
h_{FE} $V_{CE(sat)}$ $V_{BE(on)}$	DC Current Gain Collector-Emitter Saturation Voltage Base-Emitter On Voltage IGNAL CHARACTERISTICS	$\begin{array}{c} \textbf{547A} \\ \textbf{547B} \\ \textbf{547C} \\ \\ \textbf{I}_{C} = 10 \text{ mA, I}_{B} = 0.5 \text{ mA} \\ \textbf{I}_{C} = 100 \text{ mA, I}_{B} = 5.0 \text{ mA} \\ \\ \textbf{V}_{CE} = 5.0 \text{ V, I}_{C} = 2.0 \text{ mA} \\ \\ \textbf{V}_{CE} = 5.0 \text{ V, I}_{C} = 10 \text{ mA} \\ \\ \\ \textbf{I}_{C} = 2.0 \text{ mA, V}_{CE} = 5.0 \text{ V,} \\ \\ \end{array}$	110 200 420 0.58	220 450 800 0.25 0.60 0.70 0.77	V

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